Amendments to the Specification:

Please replace the paragraph, beginning at page 1, line 10, with the following rewritten paragraph:

The present invention relates to an antenna switch module, an all-in-one communication module, a communication apparatus and a method for manufacturing the antenna switch module. For instance, it relates to the antenna switch modules for high-frequency and high-power signals.

Please replace the paragraph, beginning at page 1, line 17, with the following rewritten paragraph:

In recent years, there is—has been a demand for a portable telephone supporting a multi band capable of using a plurality of methods. because of The reason for this is an expanding user base of mobile communication such as the portable telephones and globalization—of a system thereof. For instance, there is a demand for a triple-band portable telephone for using three communication methods of different frequency bands of an—ESGM (Enhanced-Global System for Mobile Communication) method mainly used in Europe, a DCS (Digital Cellular System) method increasingly used in conjunction with the expanding user base of the portable telephones and a PCS (Personal Communication Services) method mainly used in the U.S.A. Furthermore, there is a demand for a quad-band portable telephone in which a—adding_UMTS (Universal Mobile Telecommunication System) for implementing which implements a-next-generation high-speed communication—is added to them.

Please replace the paragraph, beginning at page 2, line 7, with the following rewritten paragraph:

For that reason, development is underway as to antenna switches using FET switches comprised of GaAs-field-effect transistors (hereafter, FETs) and so on capable of easily supporting the trend toward the multi band.

Please replace the paragraph, beginning at page 3, line 1, with the following rewritten paragraph:

Fig. 7 is an equivalent circuit diagram of the-FET switch operating of as SPST (Single-Pole Single-Throw) which is the a very basics basic of an antenna switch circuit. In an FET switch 10 indicated by a range enclosed by an alternate long and short dash line in Fig. 7, an FET 16 of providing a shunt circuit is connected to [[a]] ground via a capacitor 17. The FET switch 10 in the prior art used as the capacitor 17 an MIM (Metal-Insulator-Metal) capacitor formed in the semiconductor chip.

Please replace the paragraph, beginning at page 3, line 9, with the following rewritten paragraph:

The capacitor 17 is formed in the semiconductor chip by using the MIM capacitor for the following reason. To be more specific, if an impedance between the FET of the shunt circuit and the ground in the antenna switch circuit becomes high, a ground potential of the FET of the shunt circuit becomes high on operation and a high-frequency characteristic deteriorates. Thus, as shown in Fig. 7, [[a]]wiring Ls1 between the FET 16 and the capacitor 17 is rendered as small as possible in order to reduce a parasitic inductance contributing to the impedance due to a wiring Ls between the FET and the ground for the sake of preventing the impedance from becoming higher. In the case of mounting the capacitor 17 on the top surface of the dielectric layered body 45, the wiring routed on the dielectric layered body 45 becomes so long that a distance L1 cannot be short. For that reason, the capacitor 17 is formed in the semiconductor chip in which the FET is formed so as to render the wiring Ls1 shortest, and thus a wiring L shortest.

Please replace the paragraph, beginning at page 15, line 14, with the following rewritten paragraph:

Here, anAn example of a method for manufacturing the dielectric layered body 31 will now be described. Here, the The dielectric layered body will may be manufactured by using a dielectric material of an A1-Mg-Si-Gd-O system. First, a plurality of via holes are made by using mechanical punching or a laser process on green sheets made by molding slurry obtained by mixing the ceramic powder with an organic binder and an organic solvent. Next, a conductive paste of which main component is Ag (or a conductive material of low resistance such as Au or Cu) is filled in the via holes for interlayer-connecting wiring patterns formed on the green sheets.

And the wiring patterns are formed on the green sheets by a screen printing method so as to form a stripline electrode pattern and a capacitor electrode pattern.

Please replace the paragraph, beginning at page 16, line 16, with the following rewritten paragraph:

Next, the <u>The</u> electrode patterns formed in the dielectric layers will <u>now</u> be described.

Please replace the paragraph, beginning at page 16, line 18, with the following rewritten paragraph:

Fig. 3 is an exploded perspective view showing a concrete specific configuration of the antenna switch module according to the first embodiment. The dielectric layered body 31 is formed by five dielectric layers of dielectric layers L1 to L5 which are examples of a plurality of dielectric sheets of the present invention. In Fig. 3, the dielectric layers L1 to L4 are the diagrams viewed from the top surface, and the diagrams of the top surface and the under surface are shown as to the dielectric layer L5. The electrode pattern in the diagram of the under surface of the dielectric layer L5 in Fig. 3 shows a position seen through from the top surface.